The products are 15MBd high-speed opto-couplers in a plastic DIP8 package with different lead forming options. The device consists of a 850 nm AlGaAS LED, optically coupled to a very high speed integrated photo-detector logic gate with a strobable output. The output end of the product is a CMOS output, and the product has a strong common mode rejection capability. The coupled parameters are guaranteed over the temperature range of -40°C to +110°C. The products are widely used in communication interface, digital isolation for A/D, D/A conversion, high-voltage power systems, renewable energy inverters, medical imaging and patient monitoring.

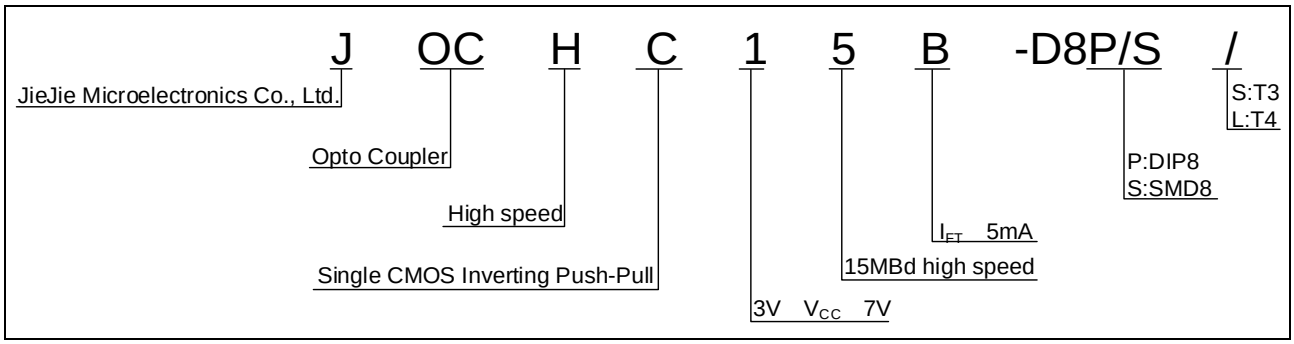
	Input Power Dissipation	P_D	100	mW
Output	Supply Voltage	V_{CC}	7	V
	Output Voltage	V_O	V_{CC}+0.5	V
	Output Current	I_O	10	mA
	Output Power Dissipation	P_O	22	mW
Total Power Dissipation		P_{tot}	130	mW
Isolation Voltage		V_{iso}	5000	Vrms
Operating Temperature		T_{opr}	-40~110	
Junction Temperature		T_j	125	
Storage Temperature		T_{stg}	-55~125	
Soldering Temperature		T_{sol}	260	

100μs pulse, 100Hz frequency
AC for 1minute, R.H.=40~60%

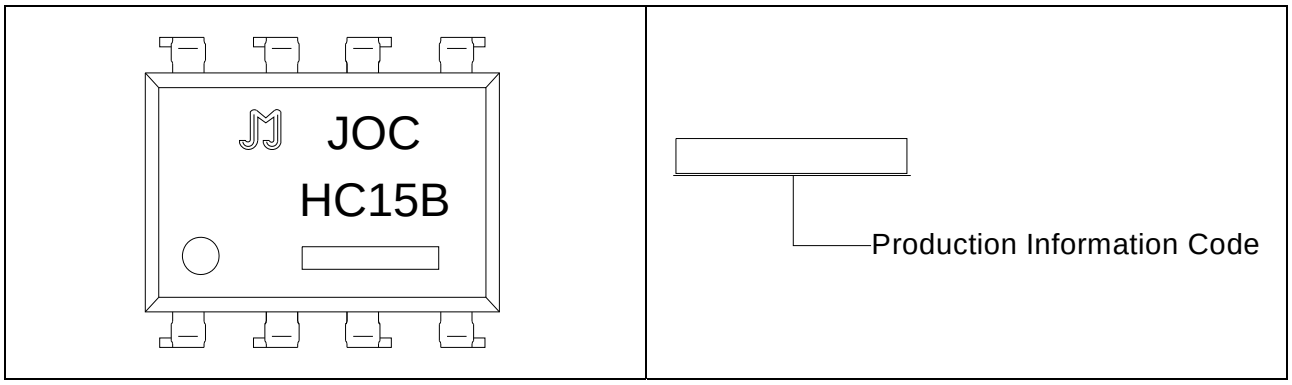
(Temperature=25°C)

	Propagation Delay Time to Logic Low	TPHL	I_F=7mA,C_L=15pF	-	70	100	ns
	Propagation Delay Time to Logic High	TPLH	I_F=7mA,C_L=15pF	-	55	100	ns
	Common Mode Transient Immunity at Logic High	CM_H	I_F=0mA, V_{CM}=1000Vpp, C_L=15pF, V_{CC}=5V	20	-	-	kV/μs
	Common Mode Transient Immunity at Logic Low	CM_L	I_F=7mA, V_{CM}=1000Vpp, C_L=15pF, V_{DD}=5V	20	-	-	kV/μs

Operating Temperature	T_a	-40	-	105	
Supply Voltage	V_{CC}	2.7	-	5.5	V
Low Level Input Current	I_{FL}	0	-	250	μA
High Level Input Current	I_{FH}	8	-	16	mA
Forward Voltage	$V_{F(OFF)}$	-	-	0.8	V



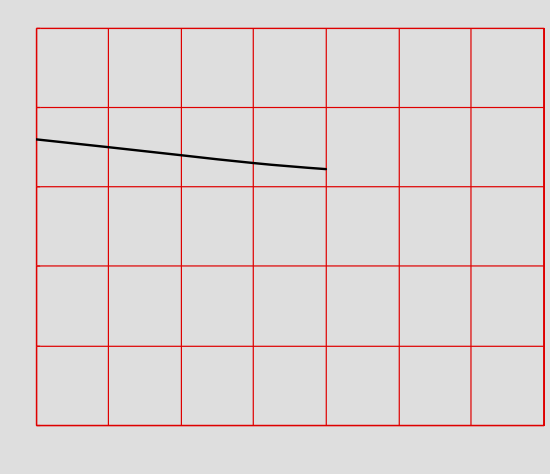
DIP	50 Units/Tube	40 Tubes/Inner box	5 Inner box/Outer box =10k Units
SMD	1200 Units/Reel	2 Reels/Inner box	5 Inner box/Outer box =12k Units



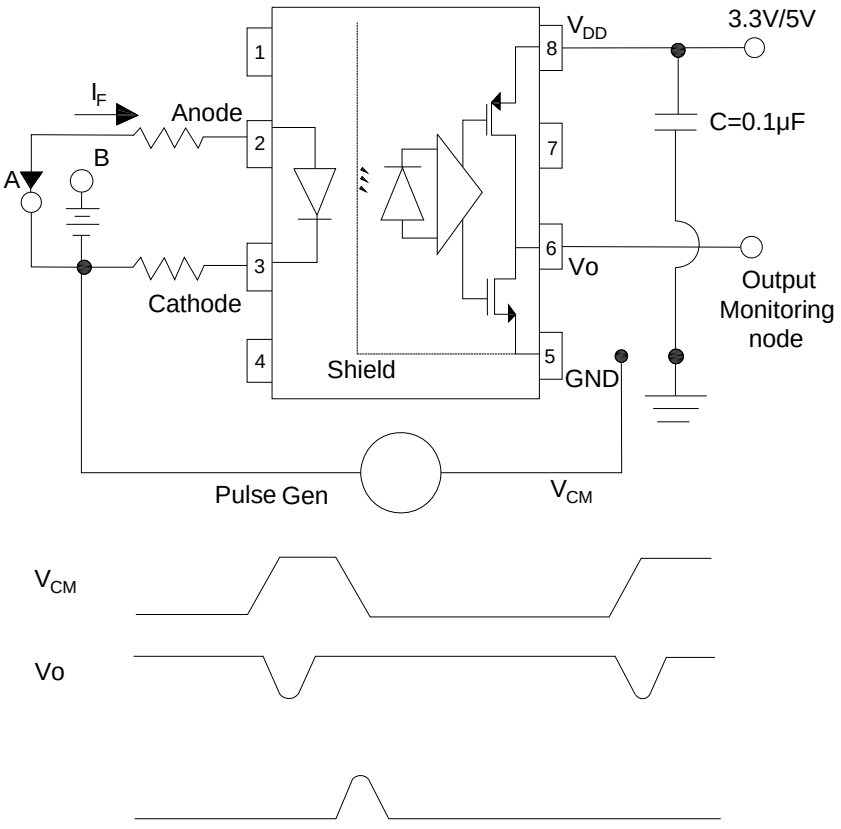
Forward Current vs. Forward Voltage

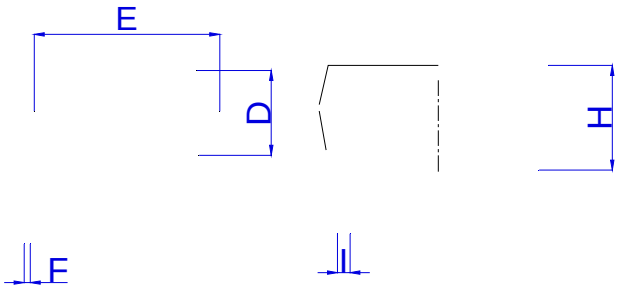
Max. Allowable LED Forward Current vs. Ambient Temperature

Propagation Delay vs. Ambient Temperature

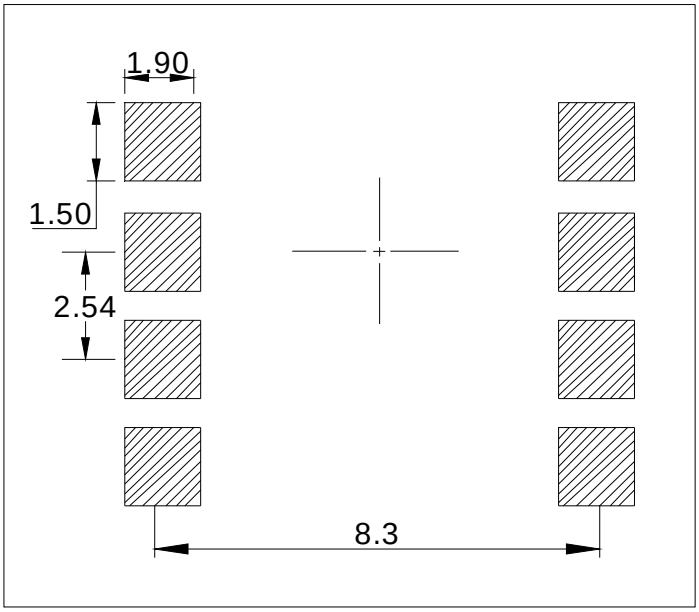


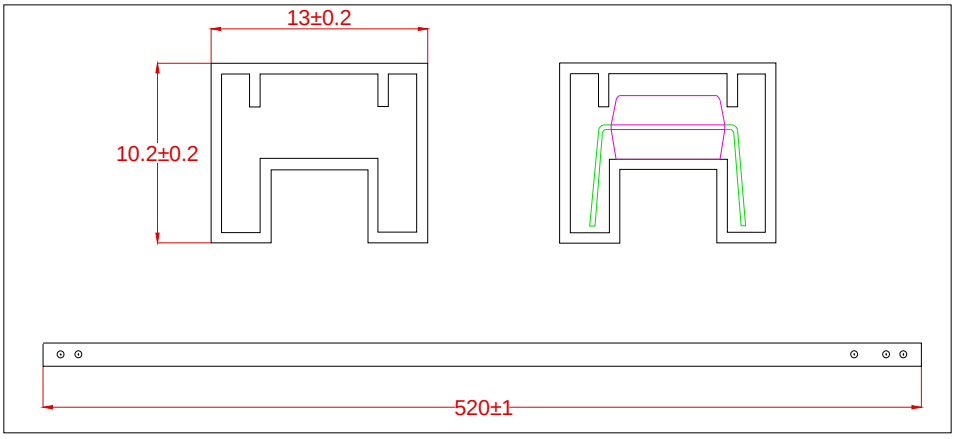
Propagation Delay vs. Ambient Temperature


1
2
3
4
8
7
6
5
I_F
Anode
A
B
Cathode
Shield
V_{DD}
3.3V/5V
C=0.1μF
Vo
Output
Monitoring
node
GND
Pulse Gen
V_{CM}
V_{CM}
Vo

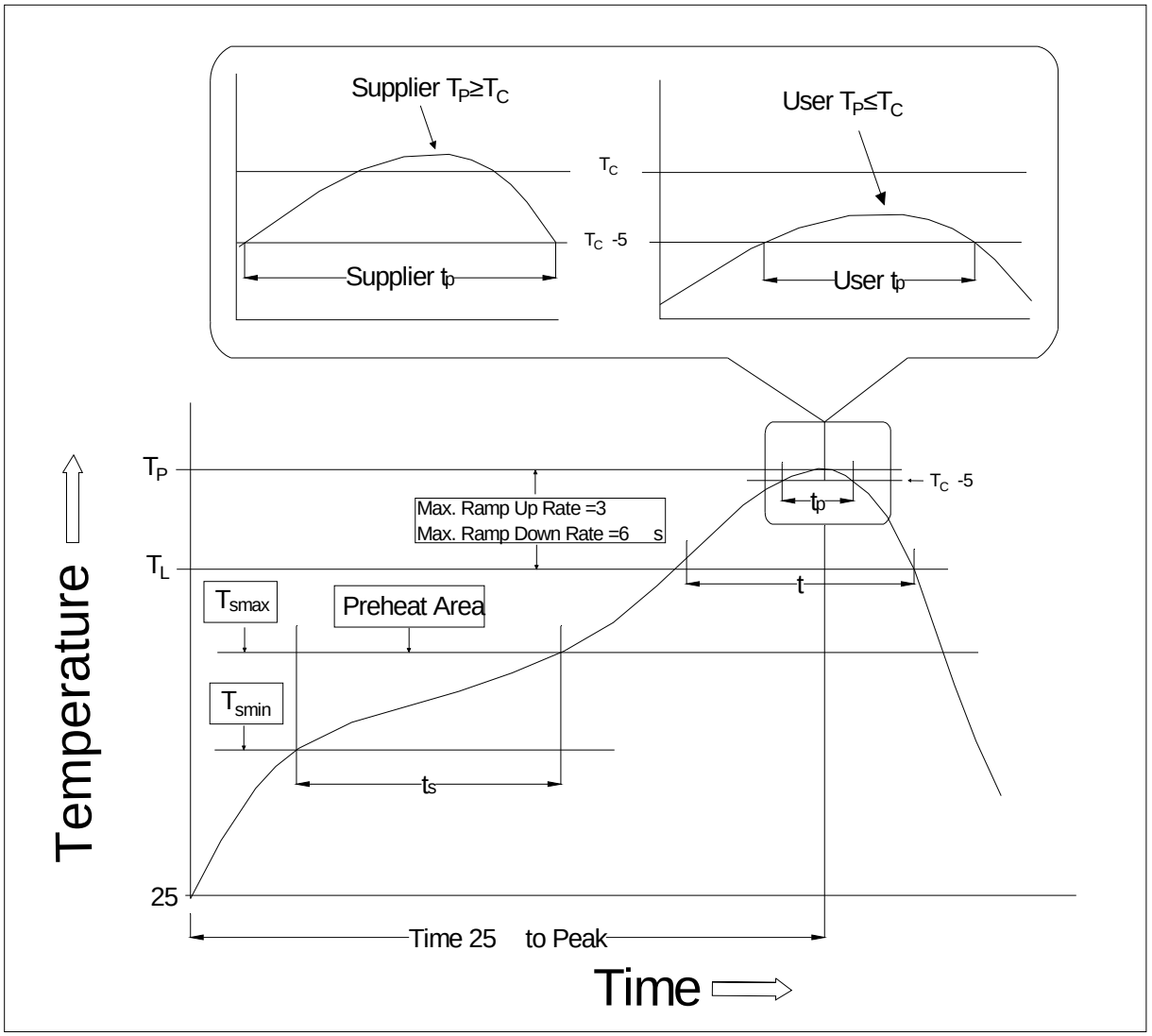


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.20		6.60	0.244		0.260
B	9.40		9.80	0.370		0.386
C	7.15		8.95	0.281		0.352
D	3.20		3.60	0.126		0.142
E	7.32		7.92	0.288		0.312
F	0.15		0.35	0.006		0.014
G	0.90		1.50	0.035		0.059
H	3.90		4.50	0.154		0.177
I	0.40		0.60	0.016		0.024
J						

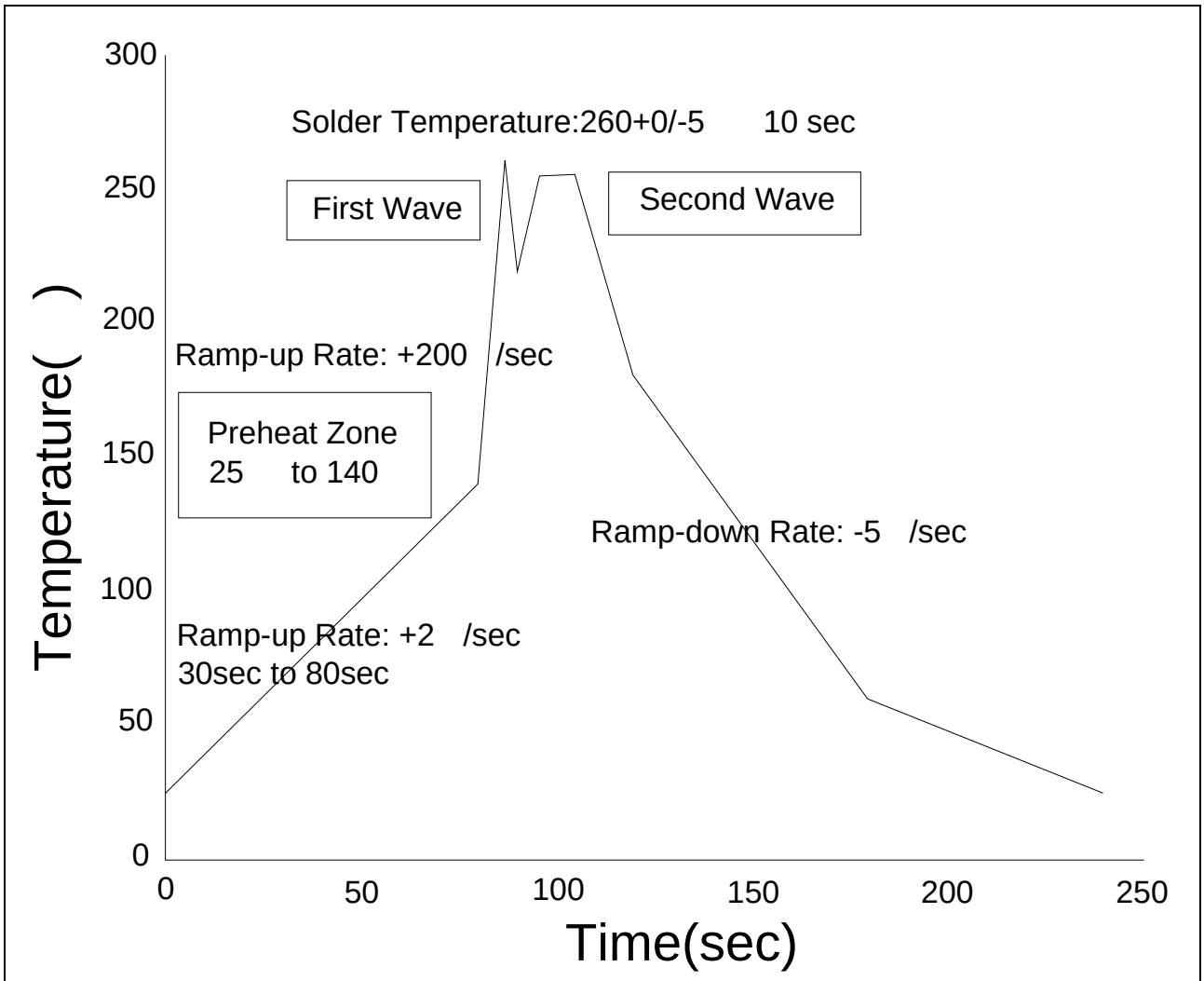

1.90
1.50
2.54
8.3


13±0.2
10.2±0.2
520±1

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Temperature Min. (Tsmin)	100	150
Temperature Max. (Tsmax)	150	200
Time (ts) from (Tsmin to Tsmax)	60-120 seconds	60-120 seconds
Ramp-up Rate (tL to tP)	3 /second max.	3 /second max.
Liquidus Temperature (TL)	183	217
Time (tL) Maintained Above (TL)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time (tP) within 5 of 260	10 seconds	10 seconds
Ramp-down Rate (TP to TL)	3-6 /second	3-6 /second
Time 25 to Peak Temperature	6 minutes max.	8 minutes max.



Soldering Temperature	360 5
Soldering Time	3s max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.

2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.

3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.

4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.

5. The component has a shelf life of one year when stored under standard conditions.

6. Recommend storage Temp.: 0~40°C;

Recommend storage humidity: <60%;

MSL level: MSL 1

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